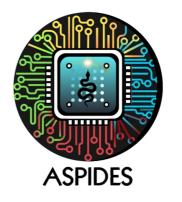
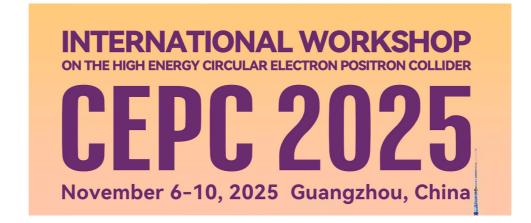
Fully digital SiPM for fast amplitude and timing measurements

L. Ratti, T.M. Floris Università di Pavia and INFN Pavia, Italy

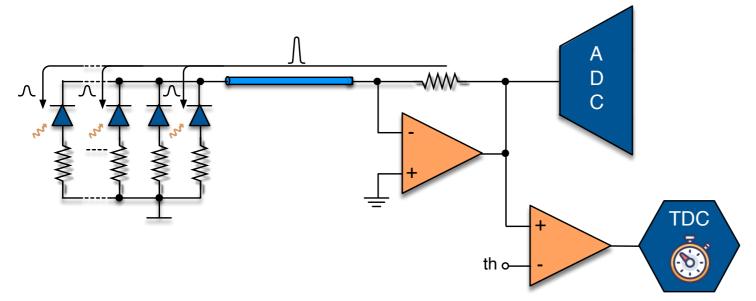
on behalf of the ASPIDES collaboration





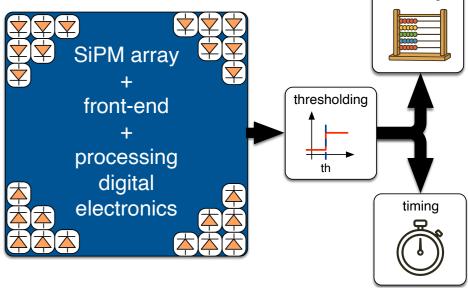


Analog vs digital SiPMs



- Direct digital vs digital-to-analog-to-digital conversion
- No random noise from analog FE, no fixed-pattern noise, no quantization noise
- Easier linearization and calibration
- Preservation of timing signal integrity local measurement of locally generated signals
- Possible issues: impact on PDE/fill factor, heat dissipation close to the sensor
- Parallel readout of current signals → analog SiPMs are much faster

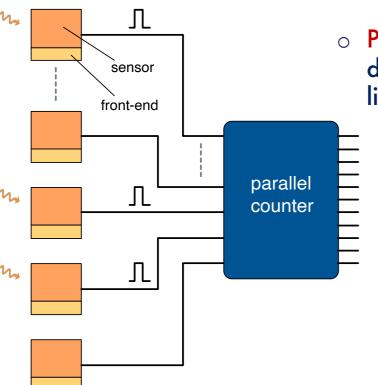
- Analog SiPMs: hybrid approach for the readout of a SPAD array, need amplification and A/D
 - best technology can be selected for both sides of the system
- Digital SiPM: typically monolithic and CMOS-based, with direct numeric readout
 - o simpler assembly phase



counting

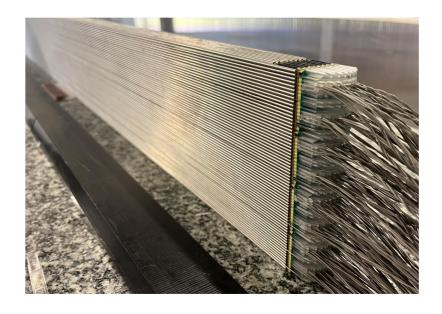
Fast counting with digital SiPMs

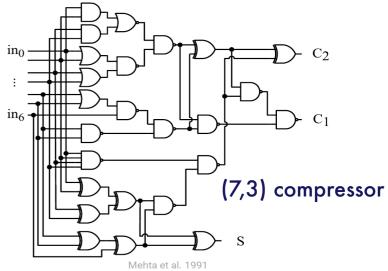
- Development of a digital SiPM for applications with scintillating fibers in dual-readout calorimetry
- Proposal: implement a digital version of the current adding architecture used in analog SiPM readout



 Parallel counter: asynchronous digital network collapsing p input lines into q output bits

- o p ₹q²-1, the output binary word representing the number of input lines set to 1
- large number of parallel connections
- trade-off between area and modularity

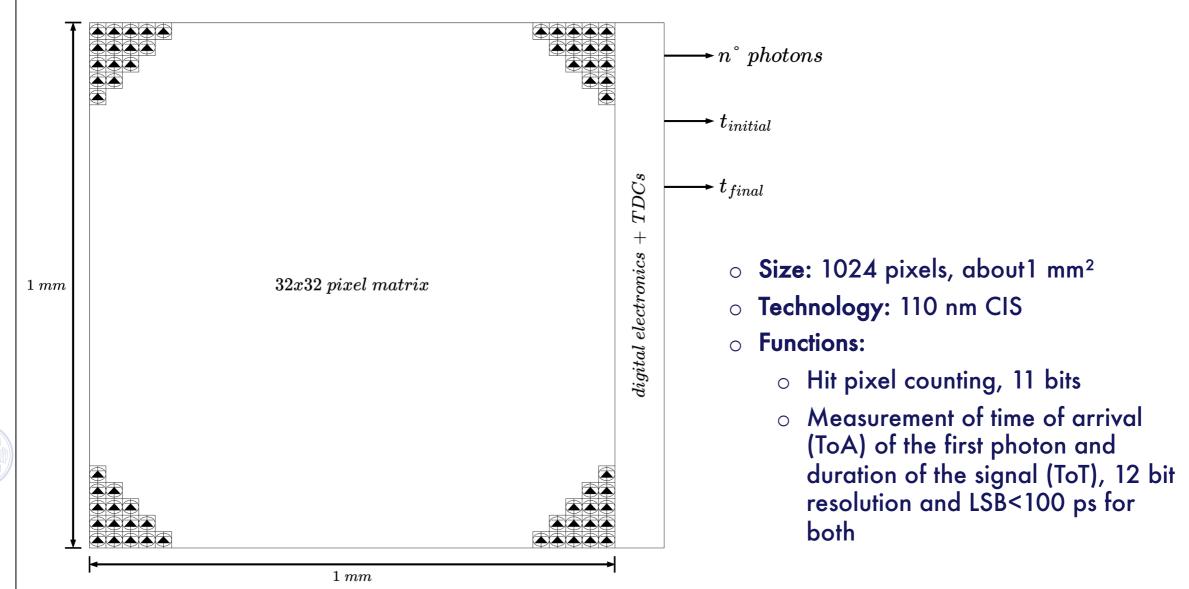




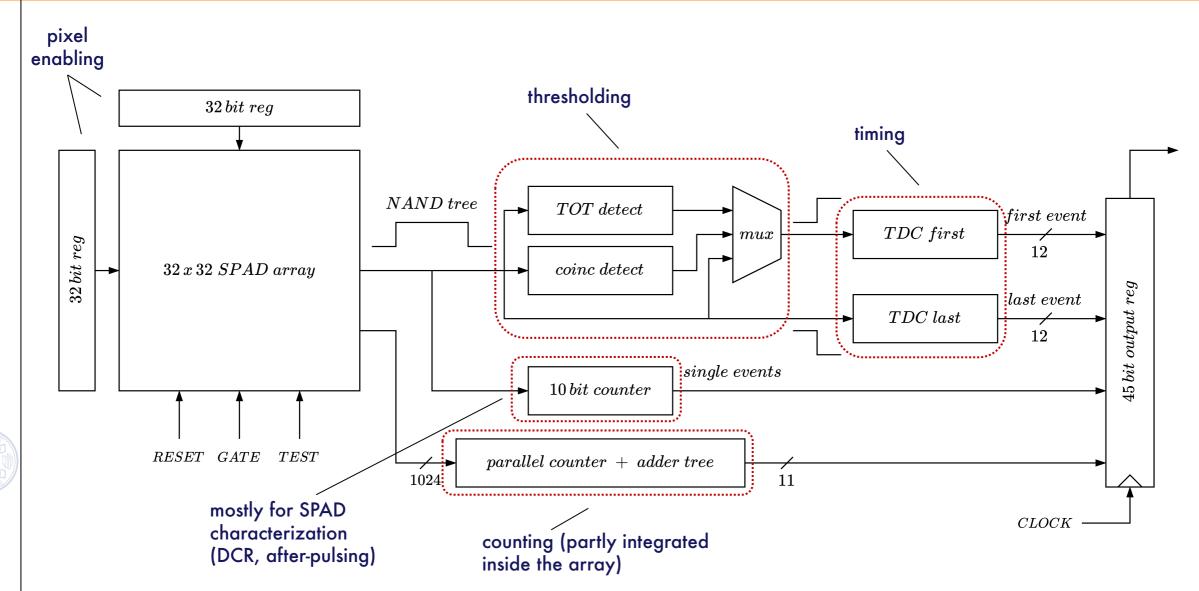
Requirements for dual-redout calorimetry

	Scintillating
Unit area (mm²)	1 x 1
Micro-cell pitch (μm)	25 to 30
Macro-pixel (μm^2)	500 x 500 (or less)
PDE (%)	≥20
DCR (kHz)	Not crucial
AP (%)	As low as possible (≈ 1)
Xtalk (%)	As low as possible (few %)
Trigger	External
Data: light intensity	Number of fired cells in 1 or 2 time windows (tenths ns long)
Data: time	Time of Arrival in the time window (< 100 ps), possibly TOT
Final - Package	Strip with 8 units
Connection	BGA

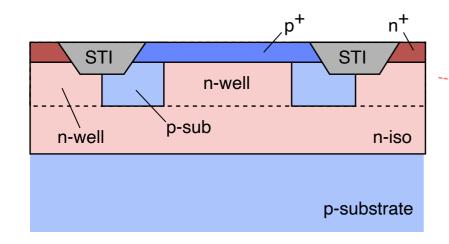
Digital SiPM prototype

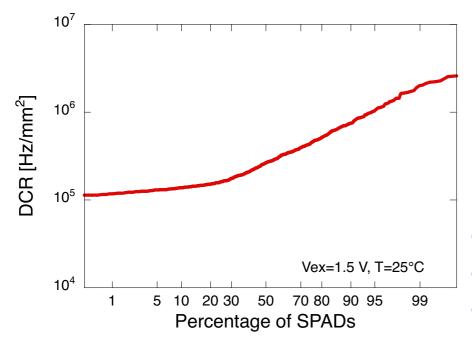


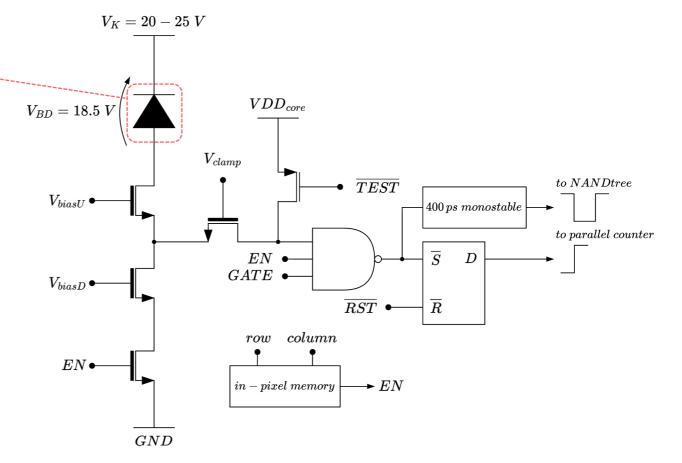
Chip architecture



SPAD and front-end

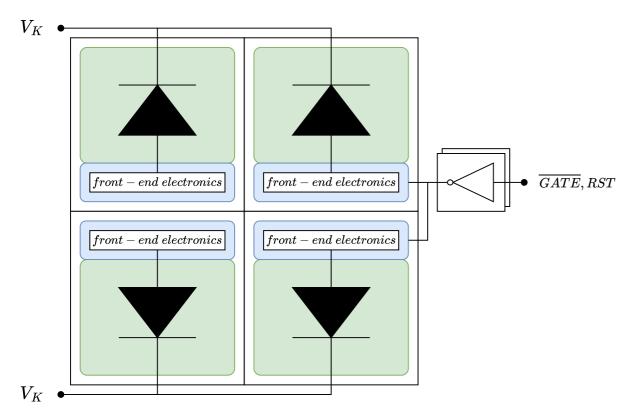




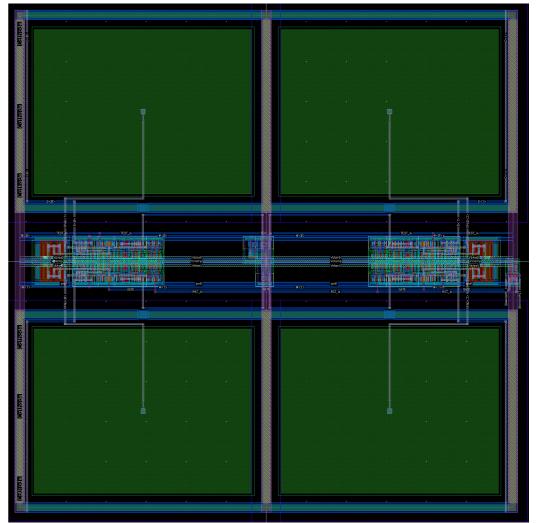


- Cascode quenching network to sustain up to 6 V excess voltage
- Individual pixels can be enabled/disabled
- Global gate signal

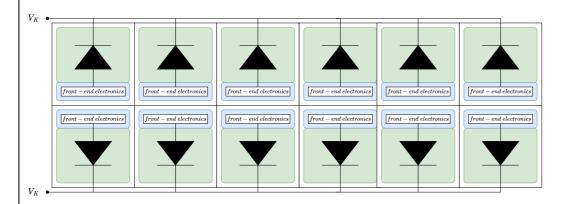
Macro-pixel

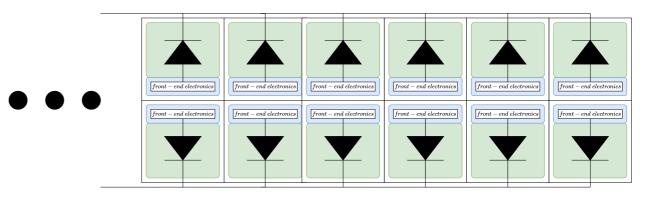


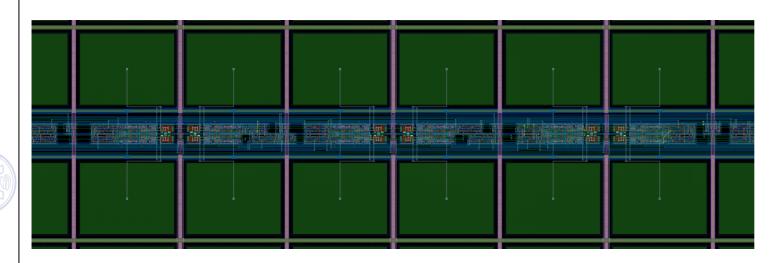
- Macropixel with 4 pixels sharing n-well and bias for fill-factor optimization (50%)
- o 30 µm pitch pixel, active area + electronics



Double-row

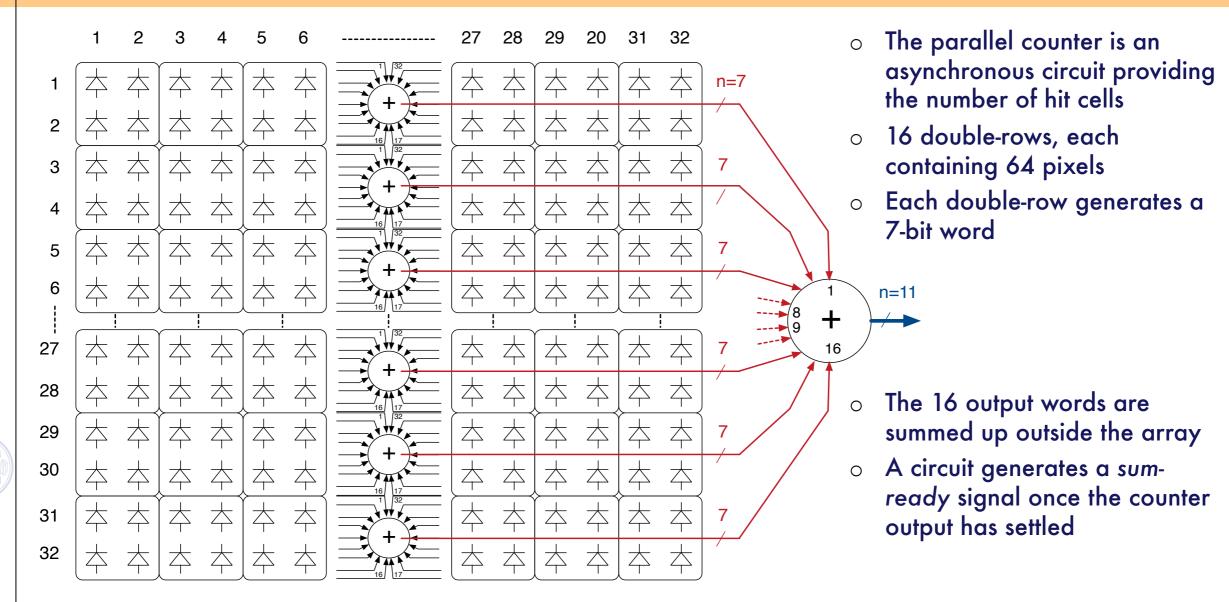




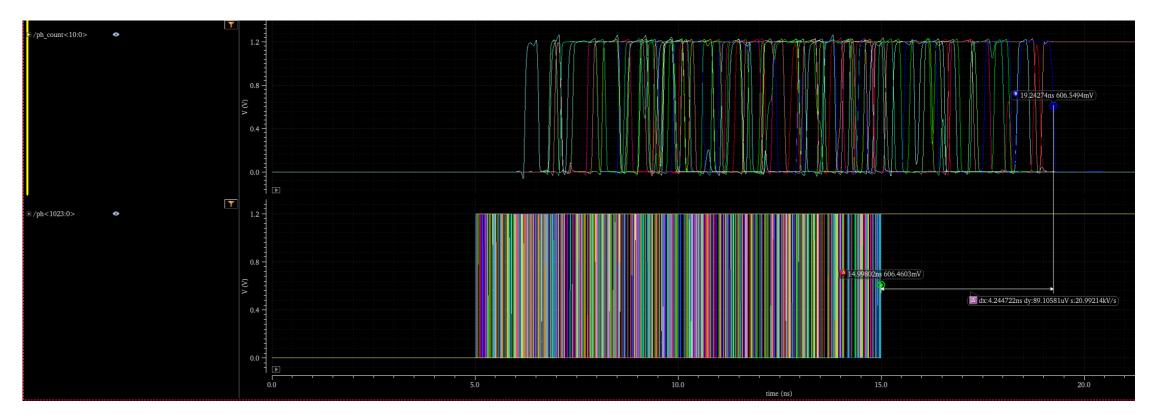


- A double-row consists of 16 macropixels and represents a counting and a timing module
- Outputs of the double-rows are combined outside the array
- Stacking 16 double-rows makes a full 32x32 array

Parallel counter architecture

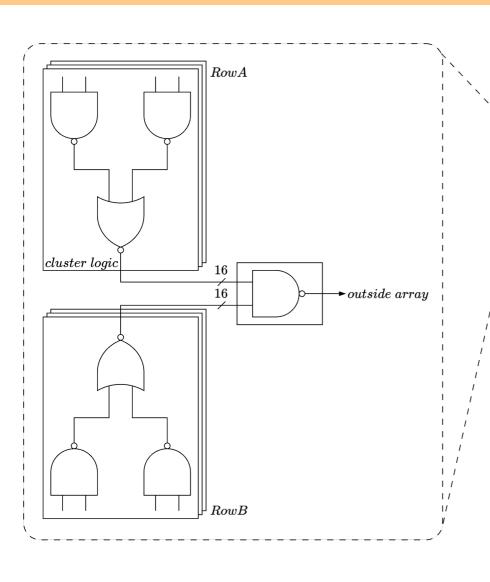


Parallel counter simulations - signal settling

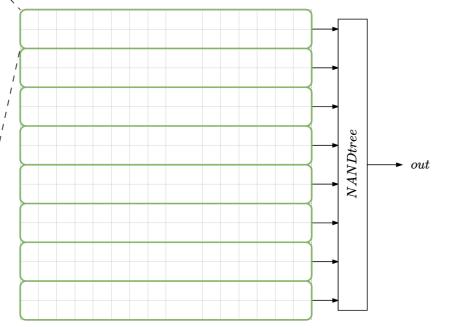


- Case of all of the pixels (1024) hit randomly within 10 ns (t=5 ns to t=15 ns) in the slow-slow corner: delay between last photon and signal settling at the counter output
 - 4.2 ns from schematic simulations (picture above)
 - 15.8 ns from post-layout simulations if needed, delay can be reduced by increasing the driving strength of the logic gates, room still available in the array

Timing circuits - NAND tree

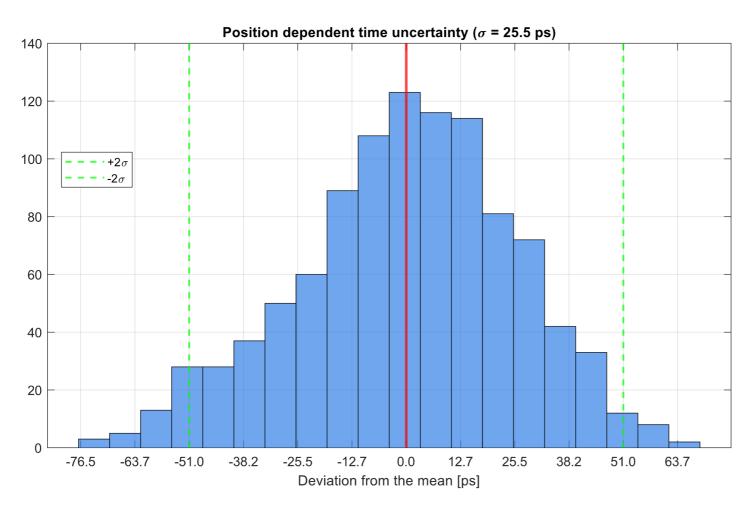


- Reads the signal from the front-end monostable
- Each double-row provides one input to the remaining tree layers outside of the array



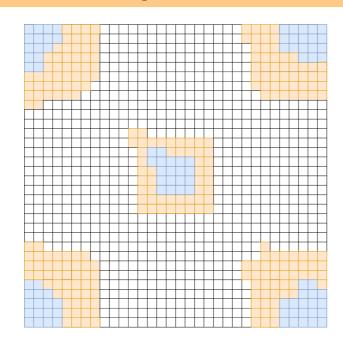
- Signal used for photon arrival timing
- Path equalization to minimize position dependent dispersion of the delay

Fixed-pattern uncertainty

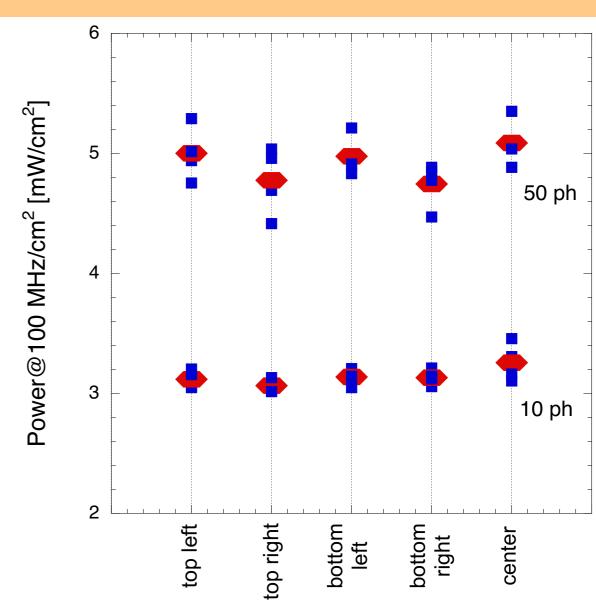


- Rising edge of NAND tree signal is used to trigger the TDC (<100 ps resolution) for photon ToA measurements
- Distribution of the rising edge time when one pixel at a time is stimulated - Std dev=25 ps (fixed-pattern time uncertainty)

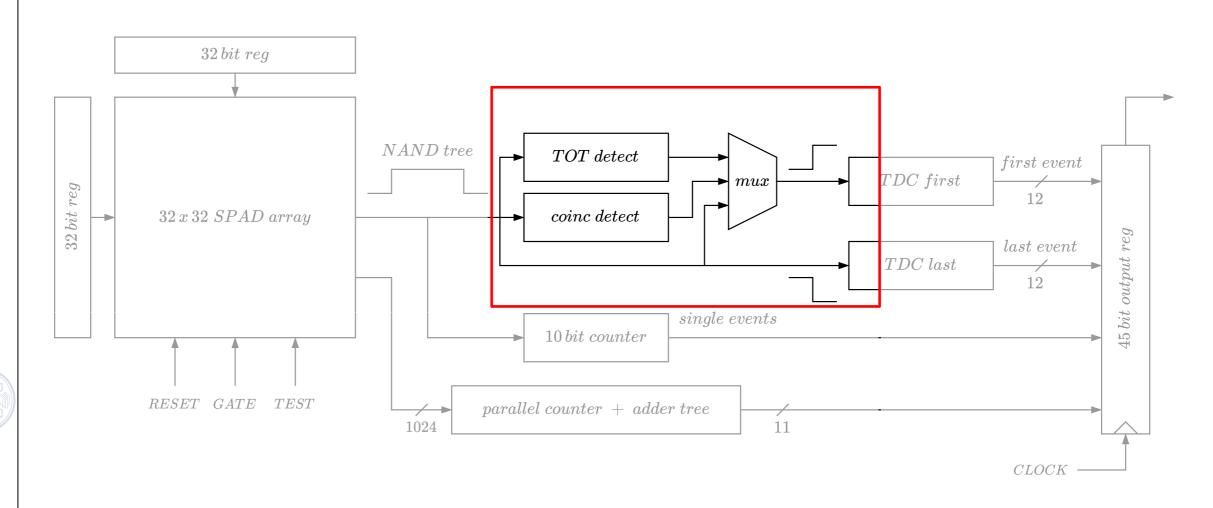
Power dissipation



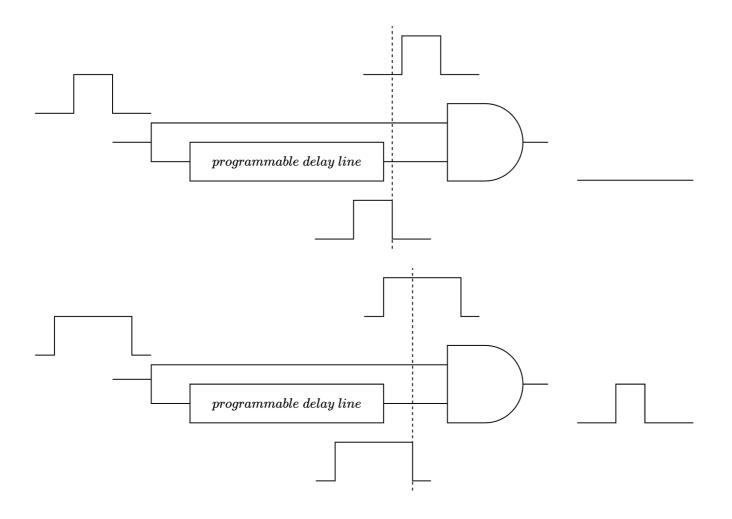
- Simulation performed on the extracted view of the entire SiPM
- Power dissipation depends on the number of hit cells and duty cycle
- Power dissipation from TDCs not included
 - about 200 pJ per TDC to convert a 200 ns time interval, corresponding to about 40 mW/cm² at a hit rate of 100 MHz/cm²



TDC triggering options



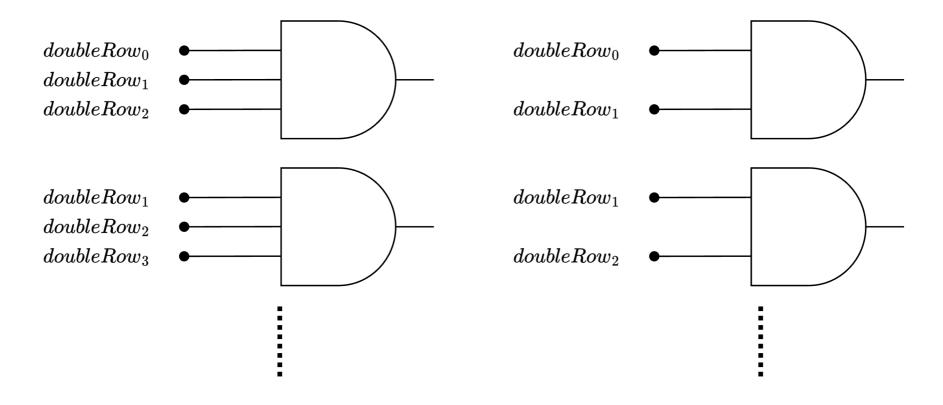
Time over threshold



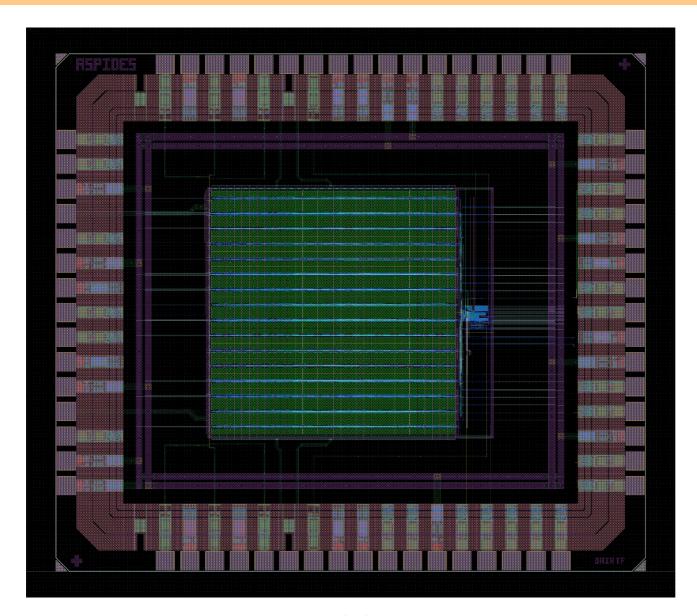
- Provides a trigger signal for the TDC in case the NAND tree signal exceeds a given duration
- o Programmable 3-bit delay line

Coincidence detection

- Provides a trigger signal to the start TDC when a coincidence is detected
 - o between two adjacent double-rows or
 - o among three adjacent double-rows



Prototype layout



- o CIS 110 nm, 6 ML 1P
- **5** mm²
- 64 PADS
 - 14 digital input
 - 14 digital output
 - o 8 bias voltage
 - o 24 power supply
 - o 4 SPAD bias
- MPW run to start in December 2025, chip expected for end Q1/beginning Q2 2026

Conclusion and outlook

- Fully digital SiPM in 110 nm CMOS under development, with potential for fast counting and ToA and ToT measurement with 100 ps resolution
 - o distributed parallel counter ensuring measurement times not exceeding a few tens of ns
 - o ToA and ToT measurement based on two 12 bits TDCs with less than 100 ps resolution
 - o different approaches available for noise mitigation, including pixel enable/disable, global gating and a few thresholding options
 - MPW run to start end of 2025
- Next steps
 - o characterization of the prototype in the first semester of 2026
 - design of a demonstrator including 8 SiPMs which can be operated based on a minimum set of I/O signals + bias
 - gathering idea for (almost) individual photon timing in a shower